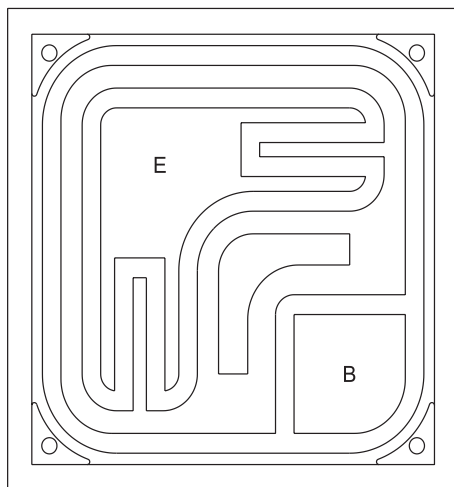


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	20 x 20 MILS
Die Thickness	8.0 MILS
Base Bonding Pad Area	4.9 x 4.9 MILS
Emitter Bonding Pad Area	6.4 x 6.4 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 16,000Å

GEOMETRY



BACKSIDE COLLECTOR R1

GROSS DIE PER 4 INCH WAFER

28,250

PRINCIPAL DEVICE TYPES

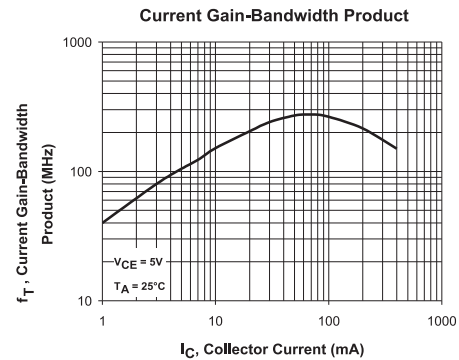
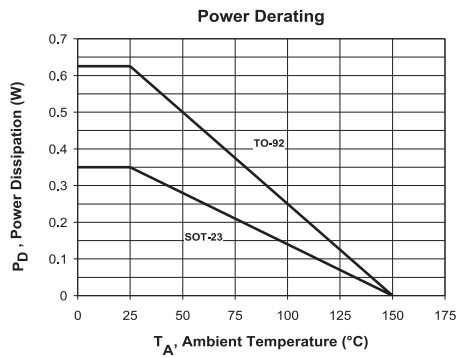
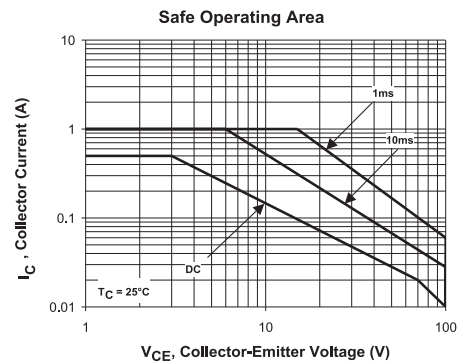
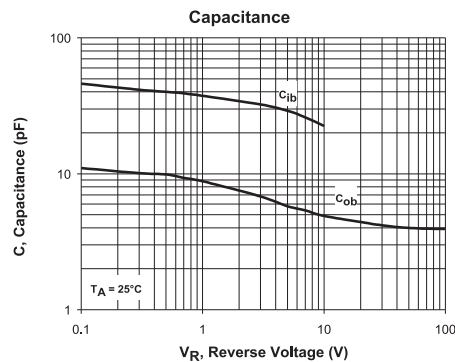
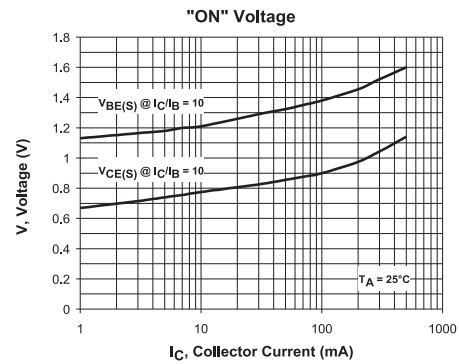
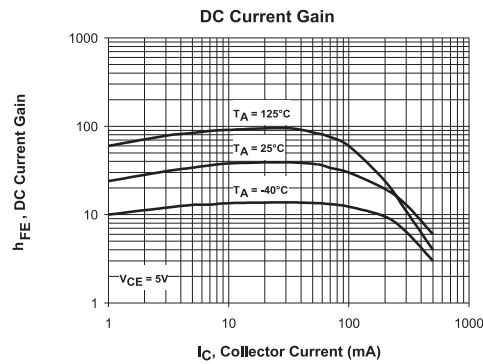
MPSA28

MPSA29

CMPTA29

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R3 (21-September 2003)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R3 (21-September 2003)